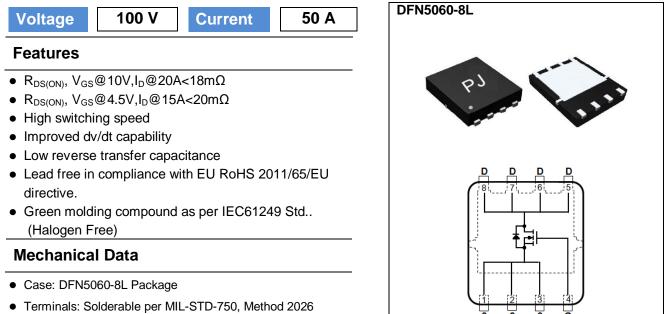
PAN	ĴΪΤ
	SEMI CONDUCTOR

100V N-Channel Enhancement Mode MOSFET



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage Gate-Source Voltage		V _{DS}	100	V	
		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C		50		
	T _C =100°C	ID	31	А	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	150		
Power Dissipation	T _c =25°C	6	83		
	T _c =100°C	PD	33	W	
Continuous Drain Current	T _A =25°C		7.5	A	
	T _A =70°C	ID	6.0	A	
Power Dissipation	T _A =25°C	5	2.0		
	T _A =70°C	PD	1.3	W	
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	156	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance ^{(Note 4,5}	5) Junction to Case	R _{θJC}	1.5	0000	
	Junction to Ambient	R _{0JA}	62.5	°C/W	

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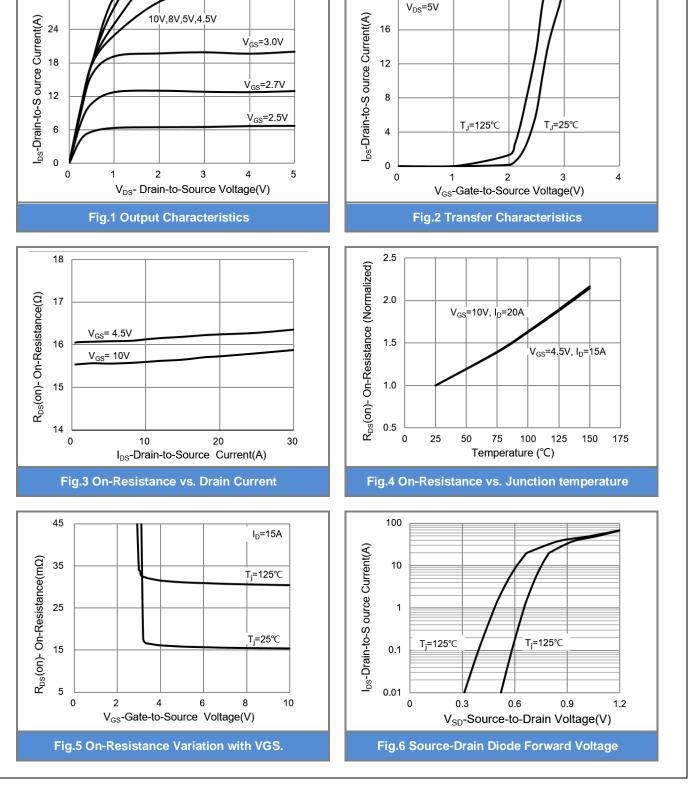


Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =20A	-	15.5	18	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V,I _D =15A	-	16	20	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V_{DS} =50V, I_{D} =30A, V_{GS} =10V ^(Note 3)	-	95	-	nC
Gate-Source Charge	Q _{gs}		-	11	-	
Gate-Drain Charge	Q _{gd}		-	18	-	
Input Capacitance	Ciss	· V _{DS} =30V, V _{GS} =0V, · f=1.0MHZ	-	5173	-	
Output Capacitance	Coss		-	226	-	pF
Reverse Transfer Capacitance	Crss		-	66	-	
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =30A, V_{GS} =10V, R_{G} =3 Ω (Note 3)	-	29	-	
Turn-On Rise Time	tr		-	61	-	
Turn-Off Delay Time	td _(off)		-	154	-	ns
Turn-Off Fall Time	t _f		-	84	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S		-	-	50	А
Diode Forward Voltage	V _{SD}	I _S =20A,V _{GS} =0V	-	0.8	1.3	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.5mH, I_{AS}=25A, V_{DD}=25V, V_{GS}=10V, R_G=25ohm, Starting T_J=25^{o}C
- 7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

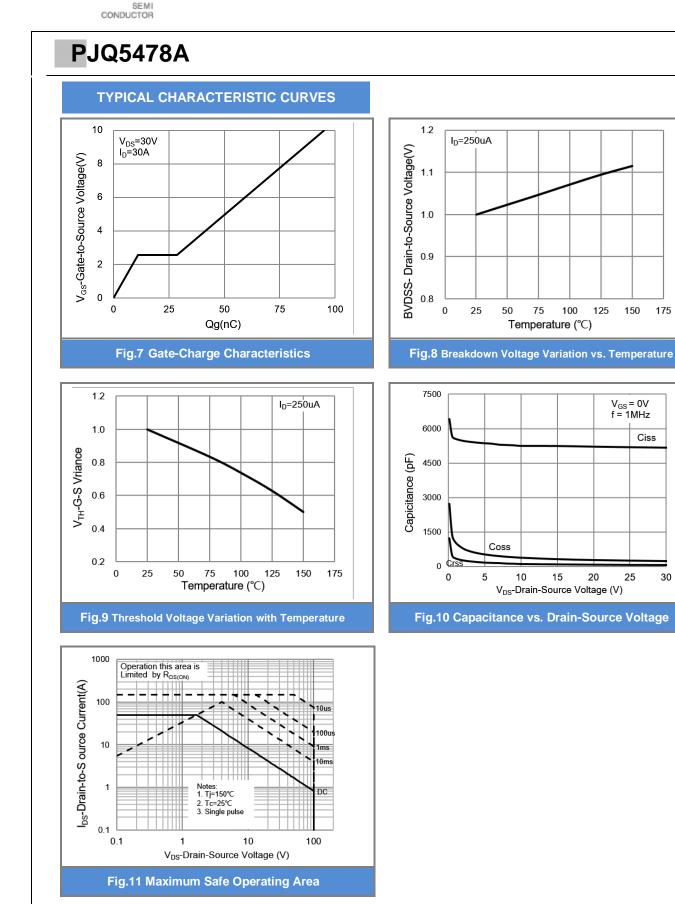
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PJQ5478A





PANJ



175

125

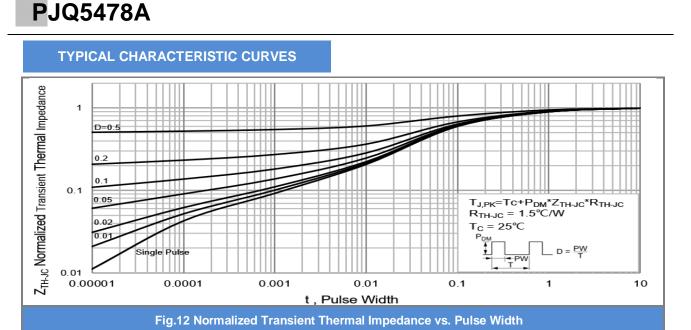
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V_{GS} = 0V f = 1MHz

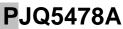
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PANJIT SEMI CONDUCTOR





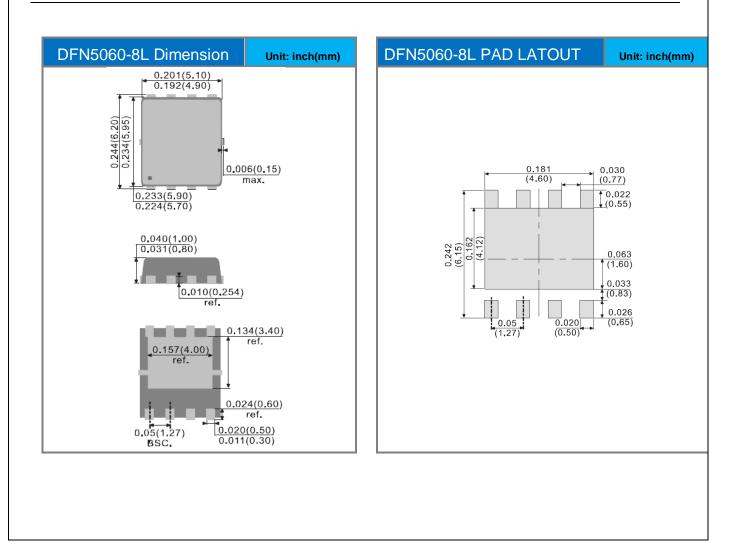




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5478A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5478A	Halogen free

Packaging Information & Mounting Pad Layout





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